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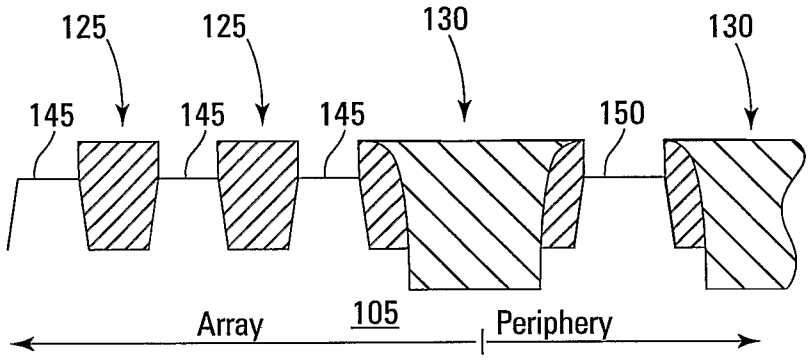
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(54) Title: MULTIPLE-DEPTH STI TRENCHES IN INTEGRATED CIRCUIT FABRICATION



(57) Abstract: Multiple trench depths within an integrated circuit device are formed by first forming trenches in a substrate to a first depth, but of varying widths. Formation of a dielectric layer can cause some of the trenches to fill or close off while leaving other, wider trenches open. Removal of a portion of the dielectric material can then be tailored to expose a bottom of the open trenches while leaving remaining trenches filled. Removal of exposed portions of the underlying substrate can then be used to selectively deepen the open trenches, which can subsequently be filled. Such methods can be used to form trenches of varying depths without the need for subsequent masking.

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